

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings of claims in the application:

**Listing of Claims:**

1. (original) A semiconductor device having a capacitor that includes a first electrode layer, a dielectric layer, and a second electrode layer is formed on a semiconductor substrate that exposes lower wiring and a lower insulating film, comprising:

an interlayer insulating film including a first electrode opening that exposes the lower wiring, and a second electrode opening adjacent to the first electrode opening that exposes a predetermined region of the lower wiring;

a first electrode formed in the first electrode opening so that the first electrode fills the first electrode opening;

a dielectric layer formed along inner walls and defining the second electrode opening;

a second electrode formed on the dielectric layer so that the second electrode fills the second electrode opening;

upper wiring formed over at least a portion of the second electrode; and

an upper insulating film formed on the interlayer insulating film surrounding the upper wiring.

2. (original) The semiconductor device of claim 1, wherein the first electrode and the second electrode are made of copper.

3. (original) The semiconductor device of claim 1, wherein the upper wiring and the lower wiring are made of copper.

4. (original) The semiconductor device of claim 1, wherein the dielectric layer is formed by layering silicone oxide and silicon nitride.

5. (original) The semiconductor substrate of claim 1, wherein the first electrode and the second electrode are each formed to have a plurality of branches that extend from a base portion.

Claims 6-12 (canceled).